

Title (en)

As/P HYBRID nLDD JUNCTION AND MEDIUM Vdd OPERATION FOR HIGH SPEED MICROPROCESSORS

Title (de)

HYBRIDER As/P-nLDD-ÜBERGANG UND MITTLERE Vdd-FUNKTIONSWEISE FÜR HOCHGESCHWINDIGKEITSMIKROPROZESSOREN

Title (fr)

JONCTION A ZONES nLDD HYBRIDES As/P AVEC FONCTIONNEMENT A TENSION D'ALIMENTATION MOYENNE POUR MICROPROCESSEURS A GRANDE VITESSE

Publication

EP 0966762 A1 19991229 (EN)

Application

EP 98904623 A 19980121

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Abstract (en)

[origin: WO9832176A1] A method of manufacturing a semiconductor device wherein hybrid nLDD regions are formed by implanting arsenic ions and phosphorous ions in source and drain regions of a substrate. The source and drain regions are formed by implanting either arsenic or phosphorous ions.

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